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# 2N5087

Preferred Device

## Amplifier Transistor

### PNP Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	50	Vdc
Collector–Base Voltage	$V_{CBO}$	50	Vdc
Emitter–Base Voltage	$V_{EBO}$	3.0	Vdc
Collector Current – Continuous	$I_C$	50	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

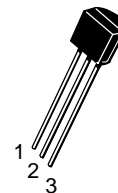
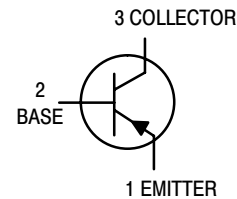
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



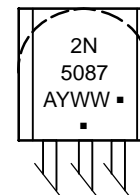
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TO-92 (TO-226)  
CASE 29  
STYLE 1

#### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
2N5087	TO-92	5000 Units/Box
2N5087G	TO-92 (Pb-Free)	5000 Units/Box
2N5087RLRA	TO-92	2000/Tape & Reel
2N5087RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

## 2N5087

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 1) ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	50	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	–	Vdc
Collector Cutoff Current ( $V_{CB} = 35\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	50	nAdc
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	50	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 100\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) (Note 1)	$h_{FE}$	250 250 250	800 – –	–
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ )	$V_{CE(sat)}$	–	0.3	Vdc
Base–Emitter On Voltage ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$V_{BE(on)}$	–	0.85	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Current–Gain — Bandwidth Product ( $I_C = 500\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 20\text{ MHz}$ )	$f_T$	40	–	MHz
Collector–Base Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{cb}$	–	4.0	pF
Small–Signal Current Gain ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	250	900	–
Noise Figure ( $I_C = 20\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 100\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 3.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	– –	2.0 2.0	dB

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

TYPICAL NOISE CHARACTERISTICS

( $V_{CE} = -5.0$  Vdc,  $T_A = 25^\circ\text{C}$ )

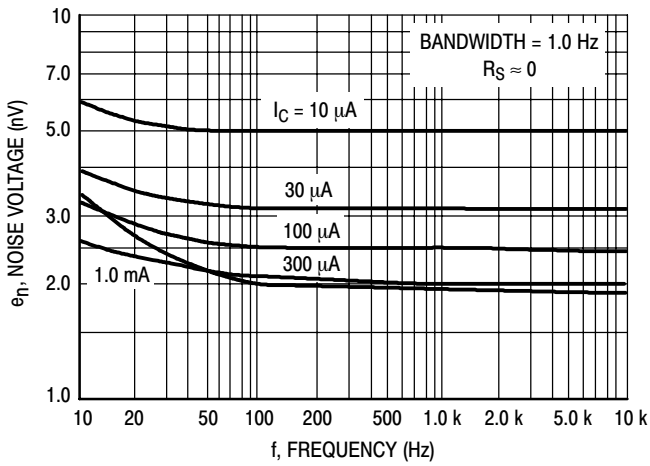


Figure 1. Noise Voltage

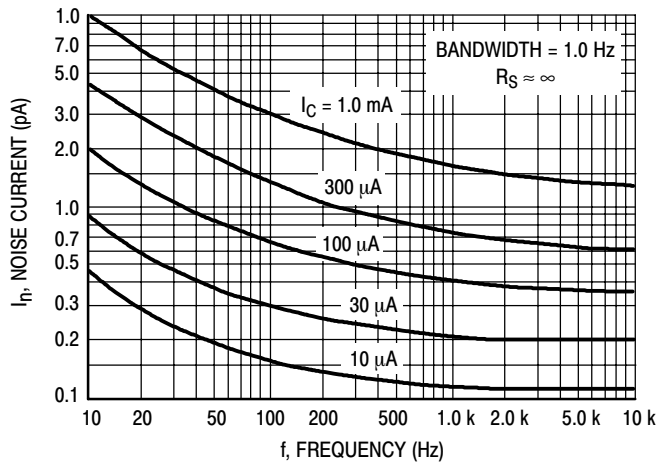


Figure 2. Noise Current

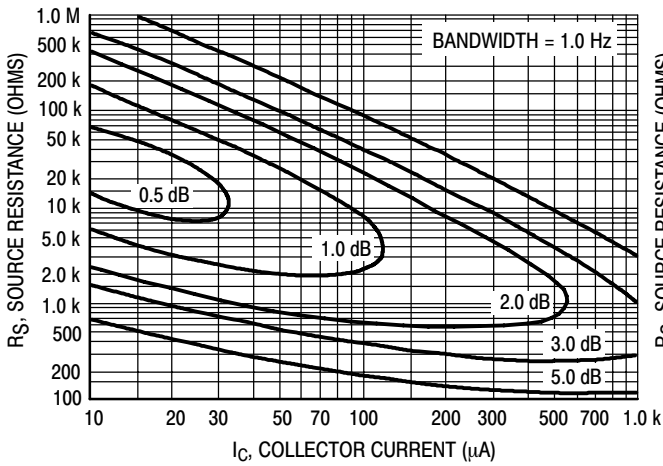


Figure 3. Narrow Band, 100 Hz

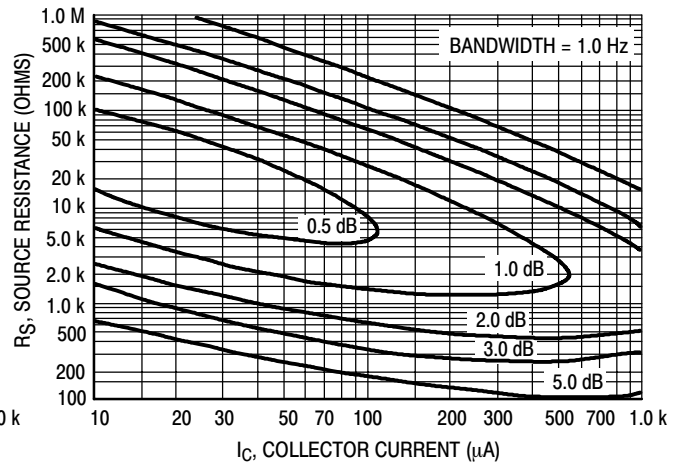


Figure 4. Narrow Band, 1.0 kHz

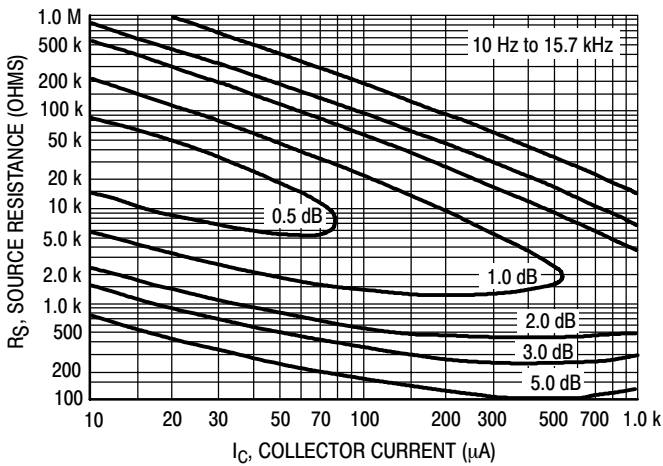


Figure 5. Wideband

Noise Figure is Defined as:

$$NF = 20 \log_{10} \left[ \frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right]^{1/2}$$

$e_n$  = Noise Voltage of the Transistor referred to the input. (Figure 3)

$I_n$  = Noise Current of the Transistor referred to the input. (Figure 4)

$K$  = Boltzman's Constant ( $1.38 \times 10^{-23}$  J/°K)

$T$  = Temperature of the Source Resistance (°K)

$R_S$  = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

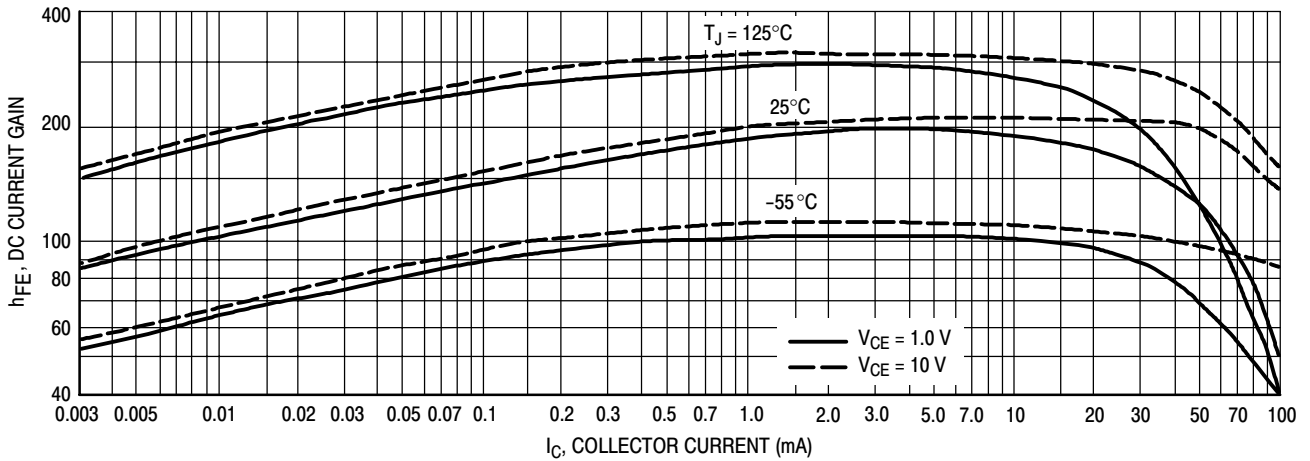


Figure 6. DC Current Gain

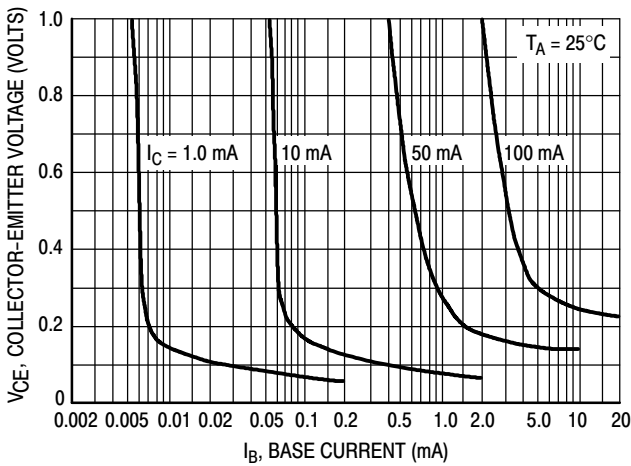


Figure 7. Collector Saturation Region

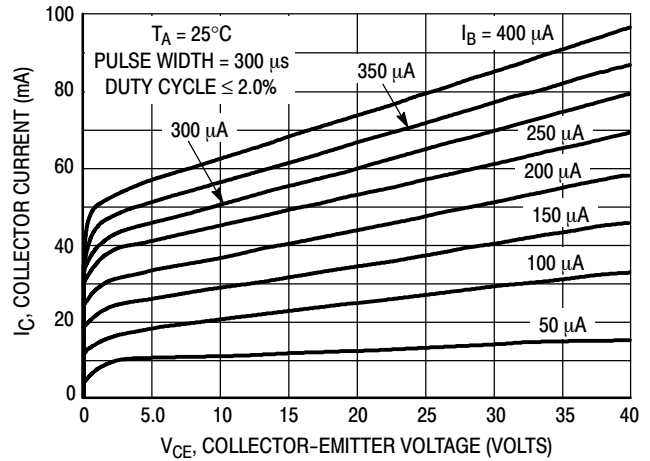


Figure 8. Collector Characteristics

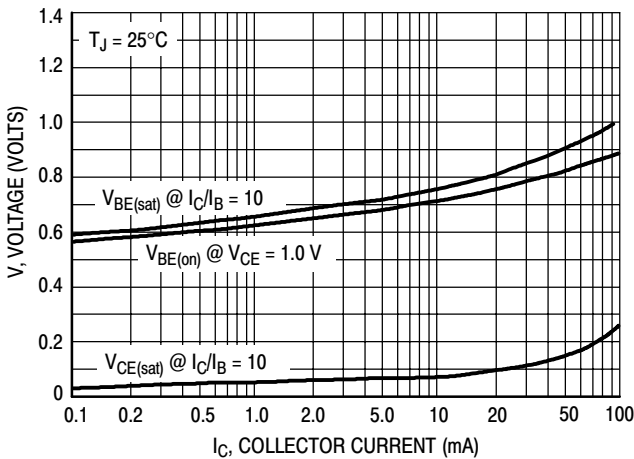


Figure 9. "On" Voltages

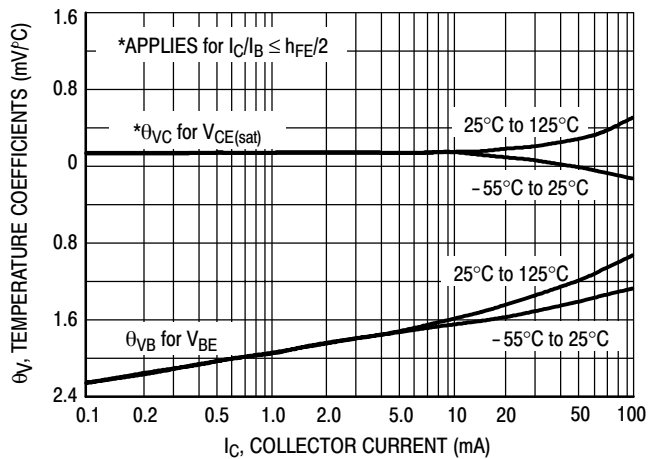


Figure 10. Temperature Coefficients

TYPICAL DYNAMIC CHARACTERISTICS

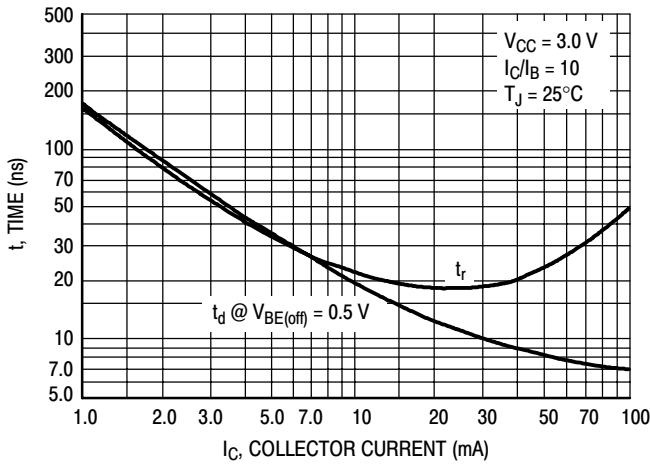


Figure 11. Turn-On Time

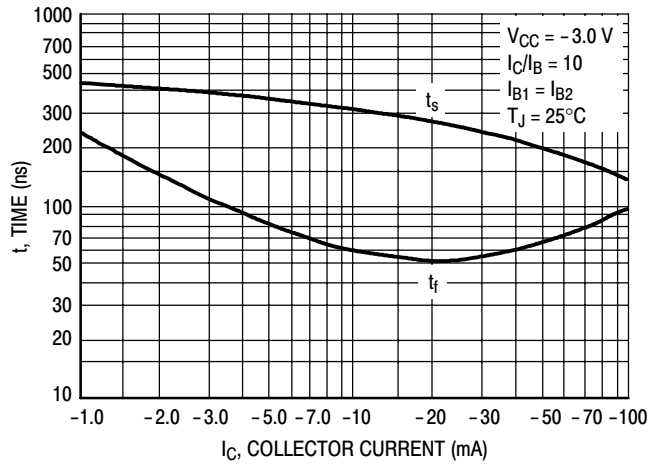


Figure 12. Turn-Off Time

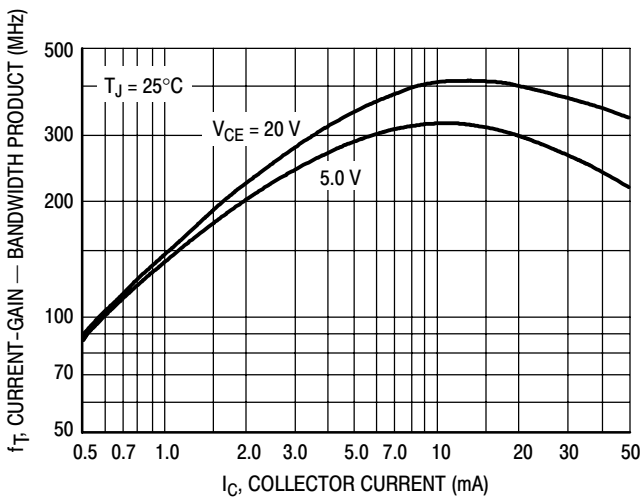


Figure 13. Current-Gain — Bandwidth Product

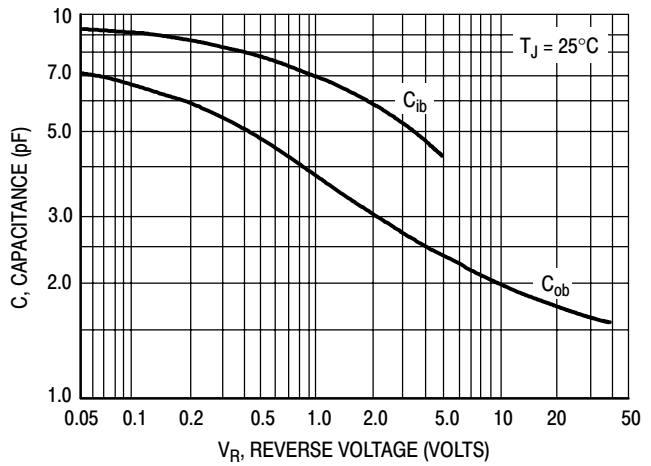


Figure 14. Capacitance

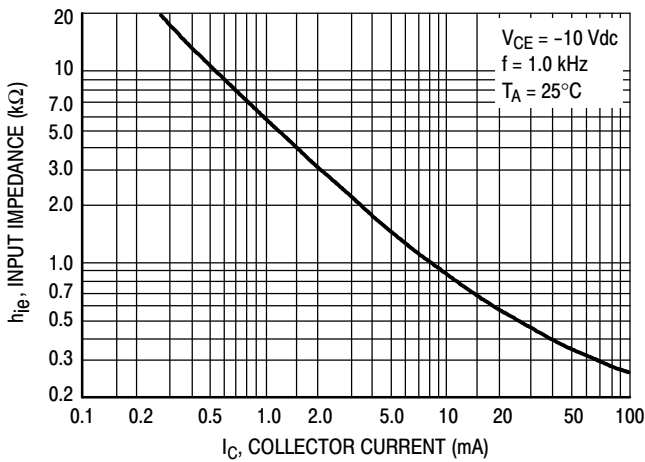


Figure 15. Input Impedance

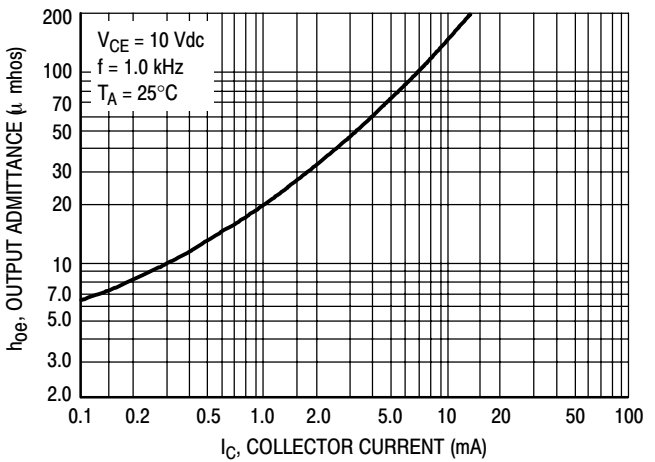


Figure 16. Output Admittance

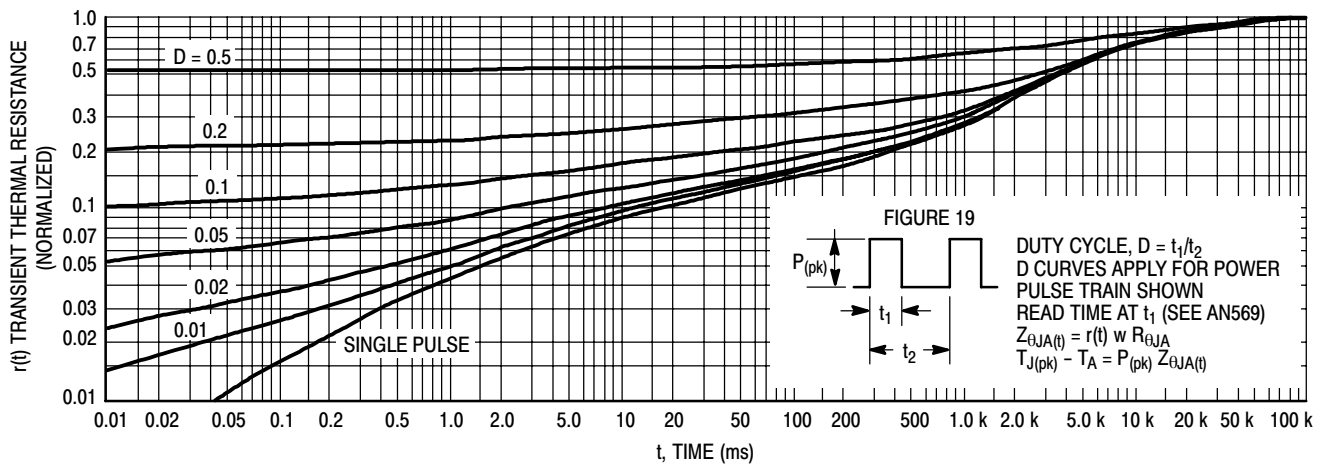


Figure 17. Thermal Response

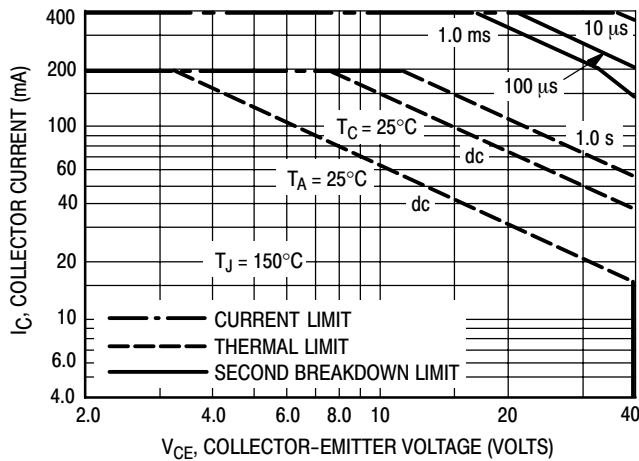


Figure 18. Active-Region Safe Operating Area

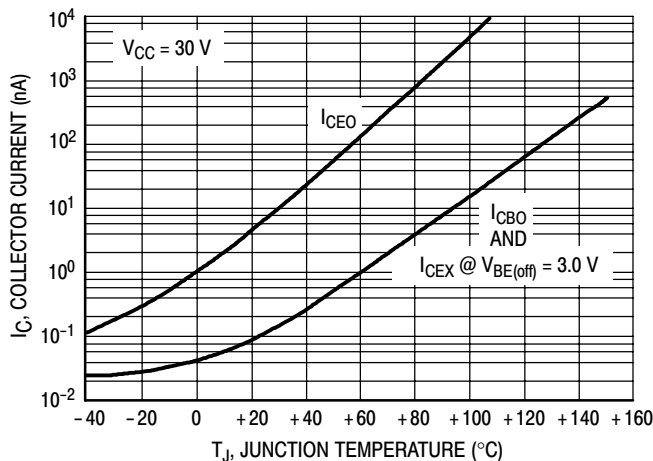


Figure 19. Typical Collector Leakage Current

The safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 18 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 17. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

**DESIGN NOTE: USE OF THERMAL RESPONSE DATA**

A train of periodical power pulses can be represented by the model as shown in Figure 19. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 17 was calculated for various duty cycles.

To find  $Z_{\theta JA}(t)$ , multiply the value obtained from Figure 17 by the steady state value  $R_{\theta JA}$ .

Example:

The 2N5087 is dissipating 2.0 watts peak under the following conditions:

$$t_1 = 1.0\text{ ms}, t_2 = 5.0\text{ ms} (D = 0.2)$$

Using Figure 17 at a pulse width of 1.0 ms and  $D = 0.2$ , the reading of  $r(t)$  is 0.22.

The peak rise in junction temperature is therefore

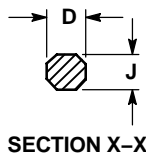
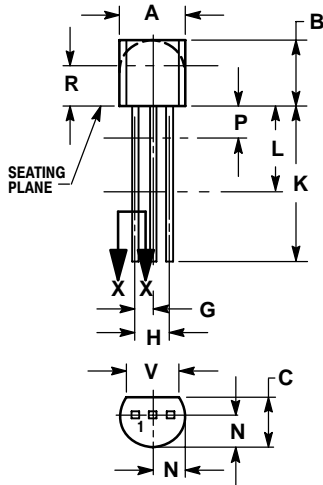
$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see ON Semiconductor Application Note AN569/D, available from the Literature Distribution Center or on our website at [www.onsemi.com](http://www.onsemi.com).

# 2N5087

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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